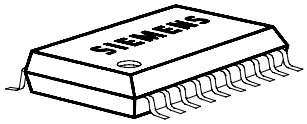
Smart Two Channel Highside Power Switch

Product Summary

Overvoltage Protection		$V_{bb(AZ)}$	43	V
Operating voltage		$V_{bb(on)}$	5.0 ... 24	V
active channels:		one	two parallel	
On-state resistance	R_{ON}	60	30	mΩ
Nominal load current	$I_{L(NOM)}$	4.0	6.0	A
Current limitation	$I_{L(NOM)}$	17	17	A

Features

- Overload protection
- Current limitation
- Short-circuit protection
- Thermal shutdown
- Overvoltage protection (including load dump)
- Reverse battery protection[1)]
- Undervoltage and overvoltage shutdown with auto-restart and hysteresis
- Open drain diagnostic output
- Open load detection in ON-state
- CMOS compatible input
- Loss of ground and loss of V_{bb} protection
- **E**lectro**s**tatic **d**ischarge (**ESD**) protection



Application

- µC compatible power switch with diagnostic feedback for 12 V DC grounded loads
- Most suitable for resistive and lamp loads
- Replaces electromechanical relays and discrete circuits

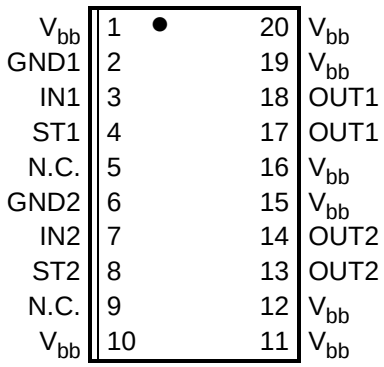
General Description

N channel vertical power FET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS® technology. Fully protected by embedded protection functions.

Pin Definitions and Functions

Pin	Symbol	Function
1,10, 11,12, 15,16, 19,20	V_{bb}	**Positive power supply voltage**. Design the wiring for the simultaneous max. short circuit currents from channel 1 to 2 and also for low thermal resistance
3	IN1	**Input 1,2**, activates channel 1,2 in case of logic high signal
7	IN2	
17,18	OUT1	**Output 1,2**, protected high-side power output of channel 1,2. Design the wiring for the max. short circuit current
13,14	OUT2	
4	ST1	**Diagnostic feedback 1,2** of channel 1,2, open drain, low on failure
8	ST2	
2	GND1	**Ground 1** of chip 1 (channel 1)
6	GND2	**Ground 2** of chip 2 (channel 2)
5,9	N.C.	**Not Connected**

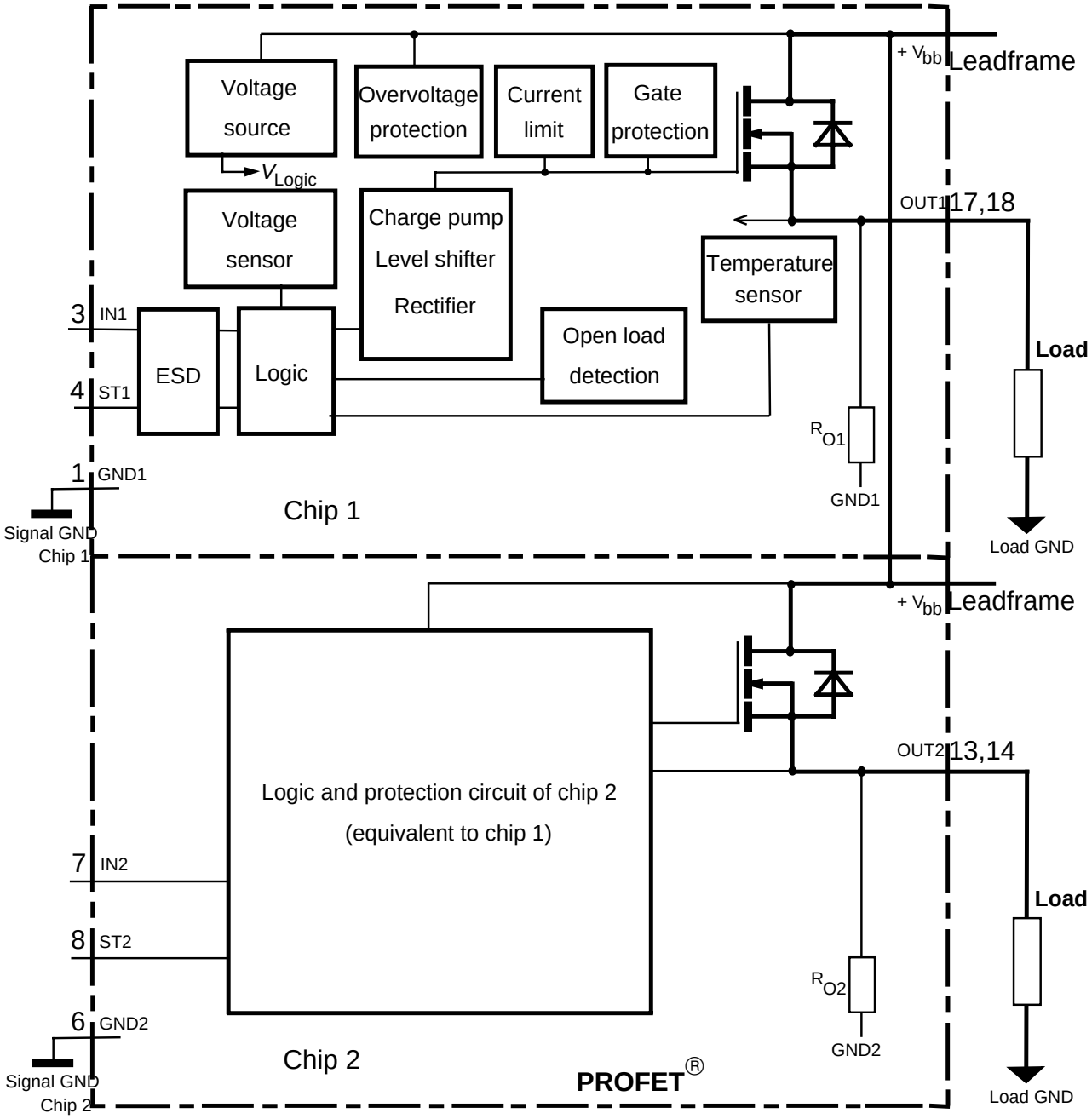
Pin configuration (top view)



1) With external current limit (e.g. resistor R_{GND}=150 Ω) in GND connection, resistor in series with ST connection, reverse load current limited by connected load.

Block diagram

Two Channels; Open Load detection in on state;



Leadframe connected to pin 1, 10, 11, 12, 15, 16, 19, 20

Maximum Ratings at T_j = 25˚C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 4)	V_{bb}	43	V
Supply voltage for full short circuit protection $T_{j,start}$ = -40 ...+150˚C	V_{bb}	24	V

Maximum Ratings at T_j = 25˚C unless otherwise specified

Parameter	Symbol	Values	Unit
Load current (Short-circuit current, see page 5)	I_L	self-limited	A
Load dump protection[2] $V_{LoadDump} = U_A + V_S$, U_A = 13.5 V R_I[3] = 2 Ω, t_d = 200 ms; IN = low or high, each channel loaded with R_L = 3.4 Ω,	$V_{Load\,dump}$[4]	60	V
Operating temperature range	T_j	-40 ...+150	˚C
Storage temperature range	T_{stg}	-55 ...+150	
Power dissipation (DC)[5] T_a = 25˚C:	P_{tot}	3.7	W
(all channels active) T_a = 85˚C:		1.9	
Electrostatic discharge capability (ESD) (Human Body Model)	V_{ESD}	1.0	kV
Input voltage (DC)	V_{IN}	-10 ... +16	V
Current through input pin (DC)	I_{IN}	±2.0	mA
Current through status pin (DC) see internal circuit diagram page 8	I_{ST}	±5.0	
Thermal resistance			
junction - soldering point[5),6)] each channel:	R_{thjs}	12	K/W
junction - ambient[5)] one channel active:	R_{thja}	41	
all channels active:		34	

Electrical Characteristics

Parameter and Conditions, each of the two channels at T_j = 25 ˚C, V_{bb} = 12 V unless otherwise specified	Symbol	Values			Unit
		min	typ	max	
Load Switching Capabilities and Characteristics					
On-state resistance (V_{bb} to OUT)					
I_L = 2 A each channel, T_j = 25˚C:	R_{ON}	--	50	60	mΩ
T_j = 150˚C:			100	120	
two parallel channels, T_j = 25˚C:			25	30	

2) Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins, e.g. with a 150 Ω resistor in the GND connection and a 15 kΩ resistor in series with the status pin. A resistor for input protection is integrated.

3) R_I = internal resistance of the load dump test pulse generator

4) $V_{Load\ dump}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

5) Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70µm thick) copper area for V_{bb} connection. PCB is vertical without blown air. See page 14

6) Soldering point: upper side of solder edge of device pin 15. See page 14

Parameter and Conditions, each of the two channels at T_j = 25 °C, V_{bb} = 12 V unless otherwise specified	**Symbol**	**Values**			**Unit**
		min	typ	max	
Nominal load current one channel active: two parallel channels active: Device on PCB[5], T_a = 85°C, $T_j \leq$ 150°C	$I_{L(NOM)}$	3.6 5.5	4.0 6.0	--	A
Output current while GND disconnected or pulled up; V_{bb} = 30 V, V_{IN} = 0, see diagram page 9	$I_{L(GNDhigh)}$	--	--	10	mA
Turn-on time to 90% V_{OUT}: Turn-off time to 10% V_{OUT}: R_L = 12 Ω, T_j =-40...+150°C	t_{on} t_{off}	80 80	200 230	400 450	µs
Slew rate on 10 to 30% V_{OUT}, R_L = 12 Ω, T_j =-40...+150°C:	dV/dt_{on}	0.1	--	1	V/µs
Slew rate off 70 to 40% V_{OUT}, R_L = 12 Ω, T_j =-40...+150°C:	$-dV/dt_{off}$	0.1	--	1	V/µs

Operating Parameters

Operating voltage[7] T_j =-40...+150°C:	$V_{bb(on)}$	5.0	--	24	V
Undervoltage shutdown T_j =-40...+150°C:	$V_{bb(under)}$	3.5	--	5.0	V
Undervoltage restart T_j =-40...+150°C:	$V_{bb(u\ rst)}$	--	--	5.0	V
Undervoltage restart of charge pump see diagram page 13 T_j =-40...+150°C:	$V_{bb(ucp)}$	--	5.6	7.0	V
Undervoltage hysteresis $\Delta V_{bb(under)} = V_{bb(u\ rst)} - V_{bb(under)}$	$\Delta V_{bb(under)}$	--	0.2	--	V
Overvoltage shutdown T_j =-40...+150°C:	$V_{bb(over)}$	24	--	34	V
Overvoltage restart T_j =-40...+150°C:	$V_{bb(o\ rst)}$	23	--	--	V
Overvoltage hysteresis T_j =-40...+150°C:	$\Delta V_{bb(over)}$	--	0.5	--	V
Overvoltage protection[8] T_j =-40...+150°C: I_{bb} = 40 mA	$V_{bb(AZ)}$	42	47	--	V
Standby current, all channels off T_j =25°C: V_{IN} = 0 T_j =150°C:	$I_{bb(off)}$	-- --	20 29	50 56	µA
Leakage output current (included in $I_{bb(off)}$) V_{IN} = 0	$I_{L(off)}$	--	--	12	µA
Operating current [9], V_{IN} = 5V, T_j =-40...+150°C $I_{GND} = I_{GND1} + I_{GND2}$, one channel on: two channels on:	I_{GND}	-- --	1.8 3.6	3.5 7	mA

7) At supply voltage increase up to V_{bb} = 5.6 V typ without charge pump, $V_{OUT} \approx V_{bb}$ - 2 V

8) see also $V_{ON(CL)}$ in circuit diagram on page 8.

9) Add I_{ST}, if I_{ST} > 0

Parameter and Conditions, each of the two channels at T_j = 25 °C, V_{bb} = 12 V unless otherwise specified	**Symbol**	**Values**			**Unit**
		min	typ	max	
Protection Functions					
Initial peak short circuit current limit, (see timing diagrams, page 11)					
each channel, T_j =-40°C:	$I_{L(SCp)}$	27	37	47	A
T_j =25°C:		20	30	40	
T_j =+150°C:		12	18	25	
two parallel channels		twice the current of one channel			
Repetitive short circuit current limit,					
$T_j = T_{jt}$ each channel	$I_{L(SCr)}$	--	17	--	A
two parallel channels		--	17	--	
(see timing diagrams, page 11)					
Initial short circuit shutdown time $T_{j,start}$ =-40°C:	$t_{off(SC)}$	--	5	--	ms
$T_{j,start}$ = 25°C:		--	4	--	
(see page 10 and timing diagrams on page 11)					
Thermal overload trip temperature	T_{jt}	150	--	--	°C
Thermal hysteresis	ΔT_{jt}	--	10	--	K
Reverse Battery					
Reverse battery voltage [10)]	$-V_{bb}$	--	--	32	V
Drain-source diode voltage (V_{out} > V_{bb}) I_L = -4.0 A, T_j = +150°C	$-V_{ON}$	--	610	--	mV
Diagnostic Characteristics					
Open load detection current, (on-condition)					
each channel, T_j = -40°C:	$I_{L(OL)}$	10	--	800	mA
T_j = 25°C:		10	--	600	
T_j = +150°C:		10	--	600	
two parallel channels		twice the current of one channel			
Open load detection voltage[11)] T_j =-40..+150°C:	$V_{OUT(OL)}$	2	3	4	V
Internal output pull down (OUT to GND), V_{OUT} = 5 V T_j =-40..+150°C:	R_O	4	10	30	kΩ

10) Requires a 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Note that the power dissipation is higher compared to normal operating conditions due to the voltage drop across the intrinsic drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 3 and circuit page 8).

11) External pull up resistor required for open load detection in off state.

Parameter and Conditions, each of the two channels at T_j = 25 °C, V_{bb} = 12 V unless otherwise specified	**Symbol**	**Values**			**Unit**
		min	typ	max	
Input and Status Feedback[12)]					
Input resistance (see circuit page 8) T_j =-40..+150°C:	R_I	2.5	3.5	6	kΩ
Input turn-on threshold voltage T_j =-40..+150°C:	$V_{IN(T+)}$	1.7	--	3.5	V
Input turn-off threshold voltage T_j =-40..+150°C:	$V_{IN(T-)}$	1.5	--	--	V
Input threshold hysteresis	$\Delta V_{IN(T)}$	--	0.5	--	V
Off state input current V_{IN} = 0.4 V: T_j =-40..+150°C:	$I_{IN(off)}$	1	--	50	µA
On state input current V_{IN} = 5 V: T_j =-40..+150°C:	$I_{IN(on)}$	20	50	90	µA
Delay time for status with open load after switch off (see timing diagrams, page 12), T_j =-40..+150°C:	$t_{d(ST\ OL4)}$	100	520	1000	µs
Status invalid after positive input slope (open load) T_j =-40..+150°C:	$t_{d(ST)}$	--	250	600	µs
Status output (open drain)					
Zener limit voltage T_j =-40...+150°C, I_{ST} = +1.6 mA:	$V_{ST(high)}$	5.4	6.1	--	V
ST low voltage T_j =-40...+25°C, I_{ST} = +1.6 mA:	$V_{ST(low)}$	--	--	0.4	
T_j = +150°C, I_{ST} = +1.6 mA:		--	--	0.6	

12) If ground resistors R_{GND} are used, add the voltage drop across these resistors.

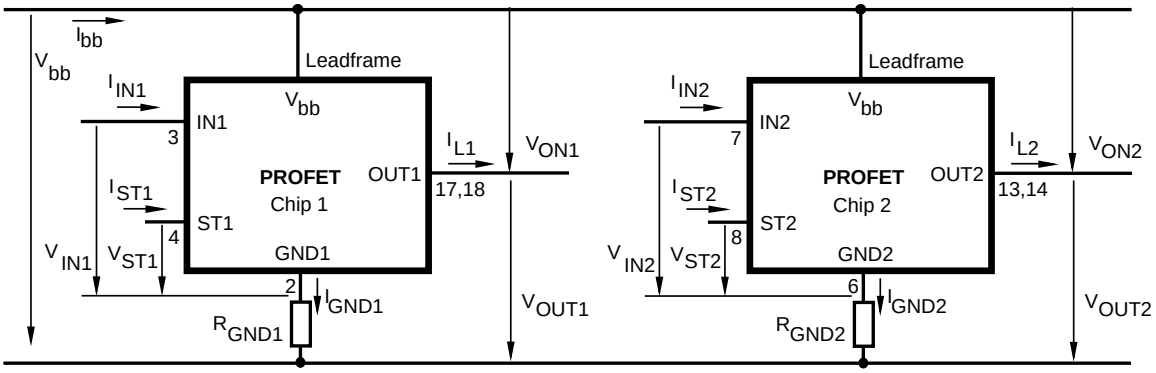
Truth Table

Cannel 1	Input 1	Output 1	Status 1
Cannel 2	Input 2	Output 2	Status 2
	level	level	BTS 725L1
Normal operation	L H	L H	H H
Open load	L H	Z H	H (L[13]) L
Short circuit to V_{bb}	L H	H H	L[14] H (L[15])
Overtem-perature	L H	L L	H L
Under-voltage	L H	L L	H H
Overvoltage	L H	L L	H H

L = "Low" Level X = don't care Z = high impedance, potential depends on external circuit
H = "High" Level Status signal valid after the time delay shown in the timing diagrams

Parallel switching of channel 1 and 2 is easily possible by connecting the inputs and outputs in parallel. The status outputs ST1 and ST2 have to be configured as a 'Wired OR' function with a single pull-up resistor.

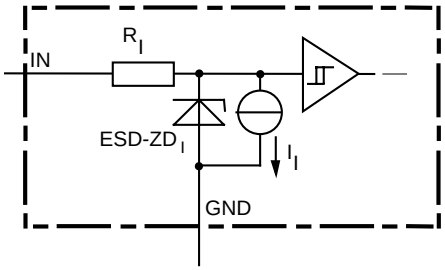
Terms



Leadframe (V_{bb}) is connected to pin 1,10,11,12,15,16,19,20
External R_{GND} optional; two resistors R_{GND1}, R_{GND2} = 150 Ω or a single resistor R_{GND} = 75 Ω for reverse battery protection up to the max. operating voltage.

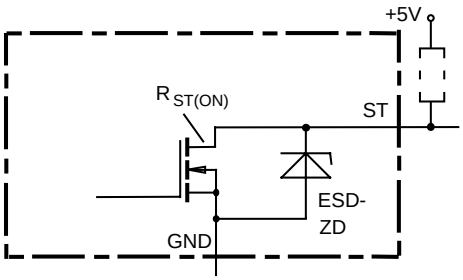
13) With external resistor between output and V_{bb}
14) An external short of output to V_{bb} in the off state causes an internal current from output to ground. If R_{GND} is used, an offset voltage at the GND and ST pins will occur and the $V_{ST\ low}$ signal may be errorious.
15) Low resistance to V_{bb} may be detected by no-load-detection

Input circuit (ESD protection), IN1 or IN2



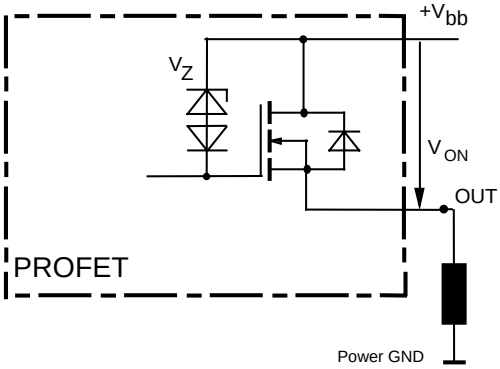
ESD zener diodes are not to be used as voltage clamp at DC conditions. Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

Status output, ST1 or ST2



ESD-Zener diode: 6.1 V typ., max 5.0 mA; $R_{ST(ON)}$ < 380 Ω at 1.6 mA, ESD zener diodes are not to be used as voltage clamp at DC conditions. Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

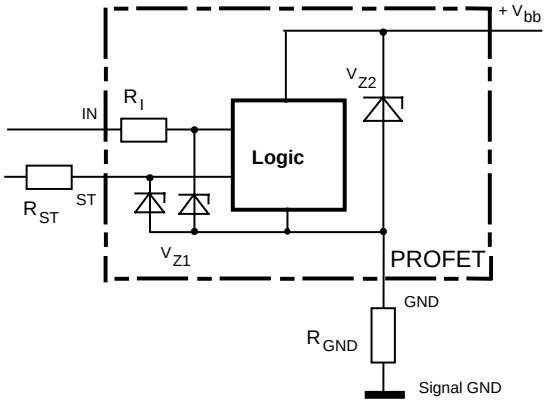
overvoltage output clamp, OUT1 or OUT2



V_{ON} clamped to $V_{ON(CL)}$ = 47 V typ.

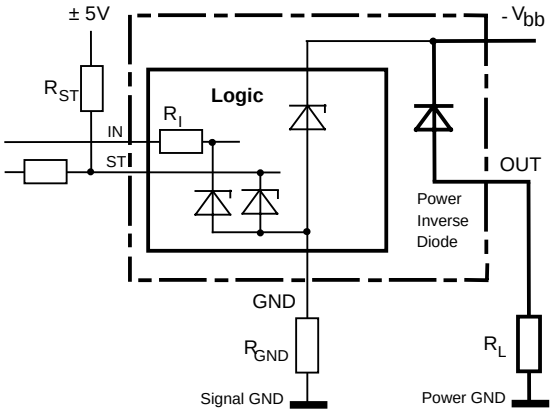
Overvoltage protection of logic part

GND1 or GND2



V_{Z1} = 6.1 V typ., V_{Z2} = 47 V typ., R_I = 3.5 kΩ typ., R_{GND} = 150 Ω, R_{ST} = 15 kΩ nominal.

Reverse battery protection



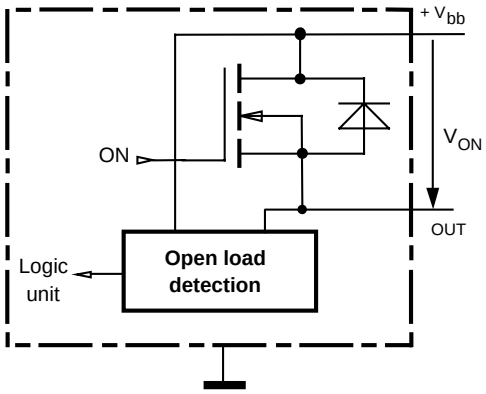
R_{GND} = 150 Ω, R_I = 3.5 kΩ typ,

Temperature protection is not active during inverse current operation.

Open-load detection, OUT1 or OUT2

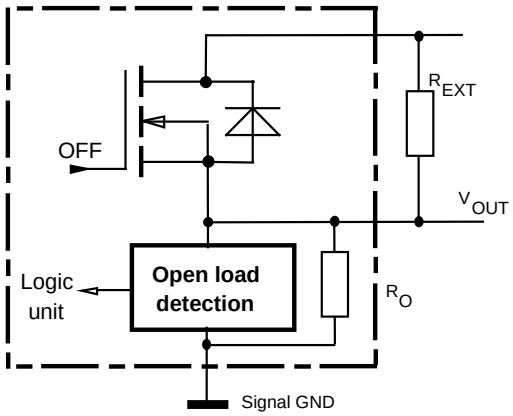
ON-state diagnostic condition:

$V_{ON} < R_{ON} \cdot I_{L(OL)}$; IN high

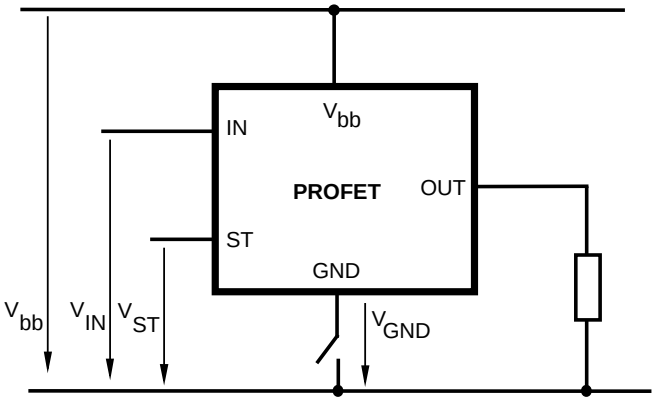


OFF-state diagnostic condition:

$V_{OUT} > 3$ V typ.; IN low

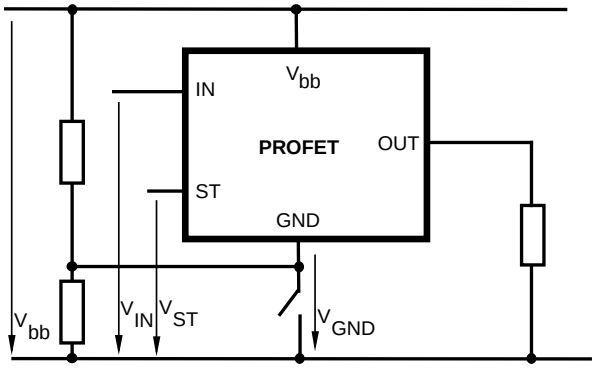


GND disconnect



In case of IN = high is $V_{OUT} \approx V_{IN} - V_{IN(T+)}$. Due to $V_{GND} > 0$, no V_{ST} = low signal available.

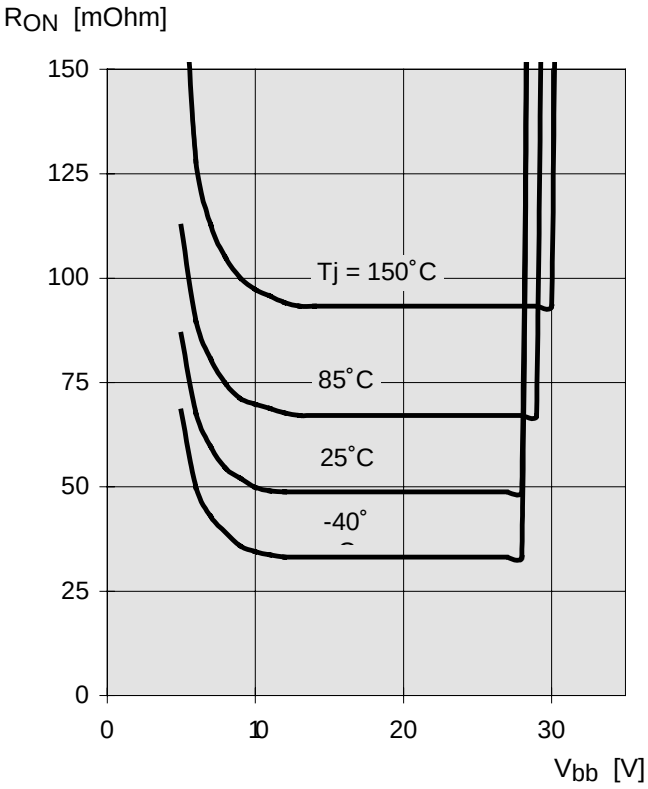
GND disconnect with GND pull up



If $V_{GND} > V_{IN} - V_{IN(T+)}$ device stays off
Due to $V_{GND} > 0$, no V_{ST} = low signal available.

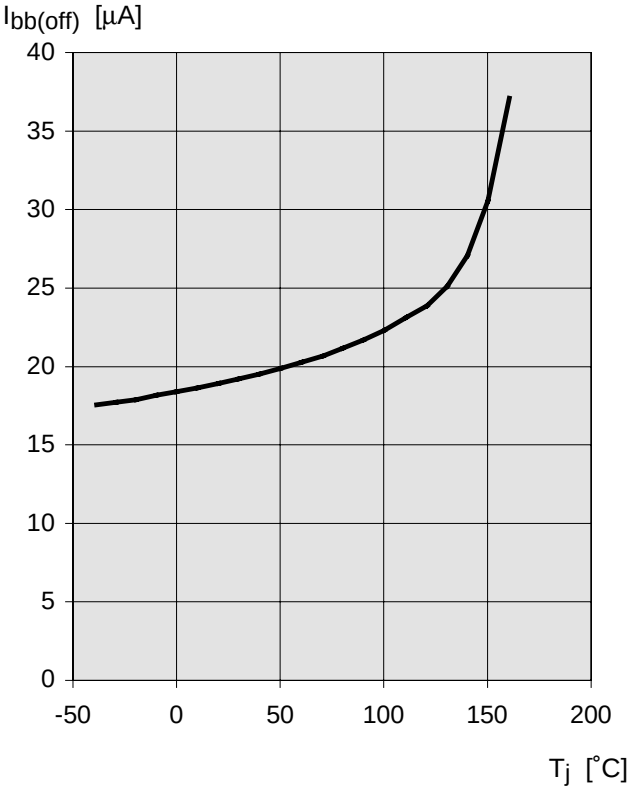
Typ. on-state resistance

$R_{ON} = f(V_{bb}, T_j)$; I_L = 2 A, IN = high



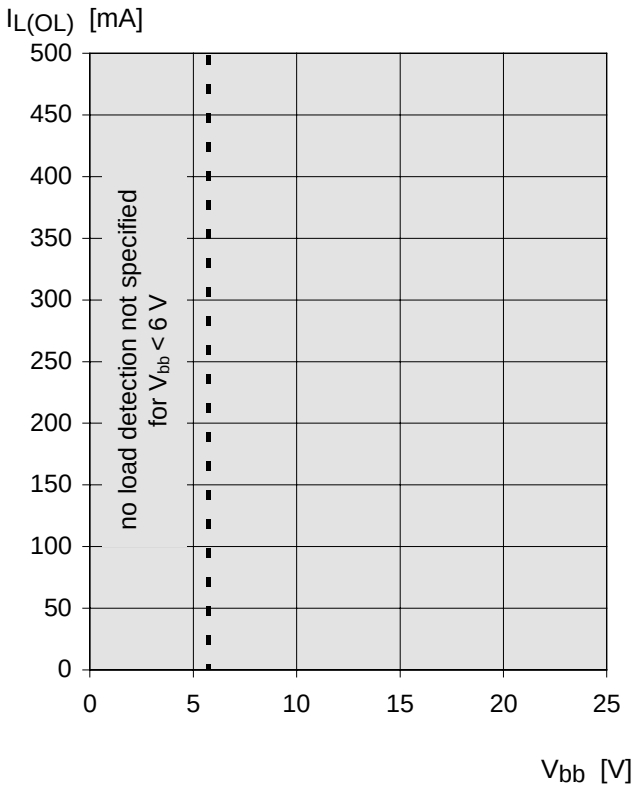
Typ. standby current

$I_{bb(off)} = f(T_j)$; V_{bb} = 9...24 V, IN1,2 = low



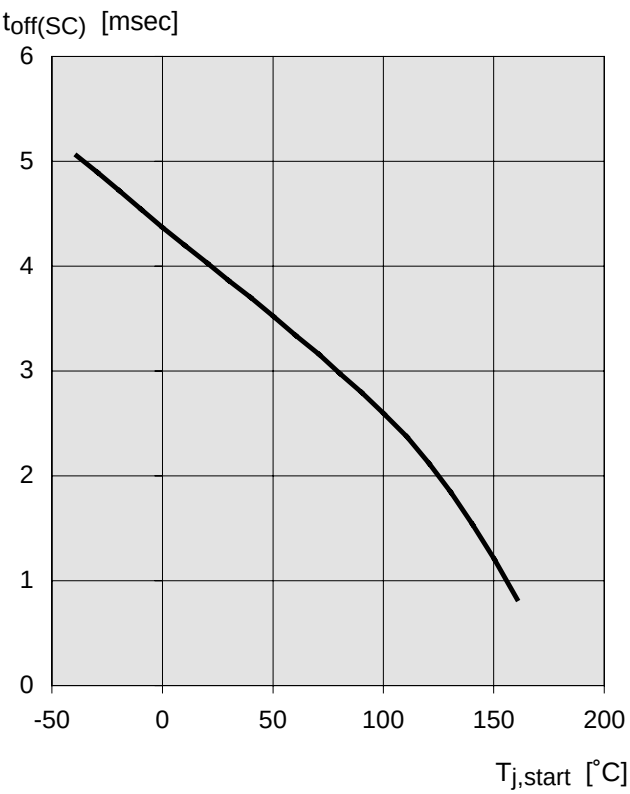
Typ. open load detection current

$I_{L(OL)} = f(V_{bb}, T_j)$; IN = high



Typ. initial short circuit shutdown time

$t_{off(SC)} = f(T_{j,start})$; V_{bb} =12 V



Timing diagrams

Both channels are symmetric and consequently the diagrams are valid for channel 1 and channel 2

Figure 1a: V_{bb} turn on:

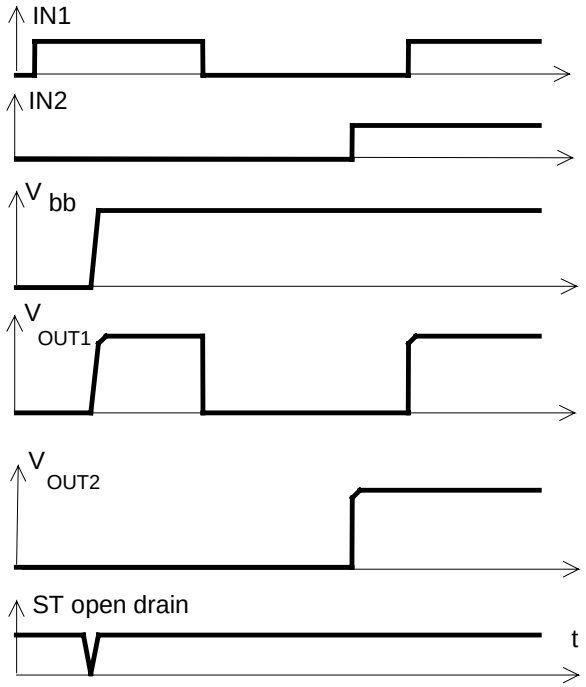
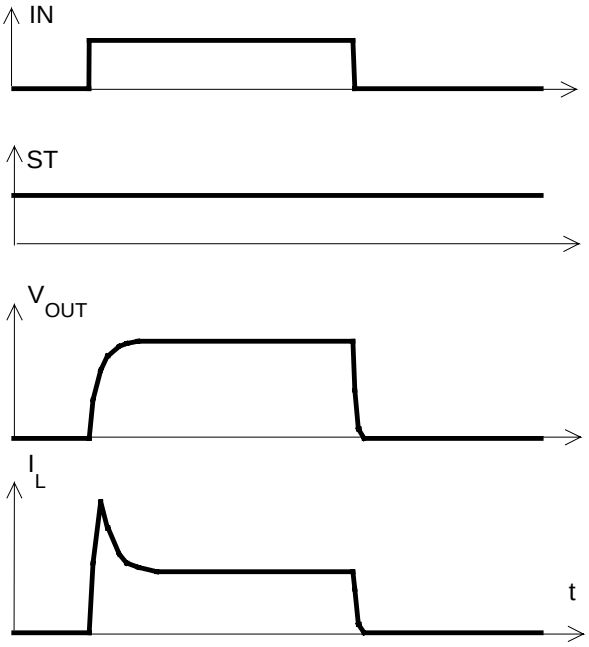
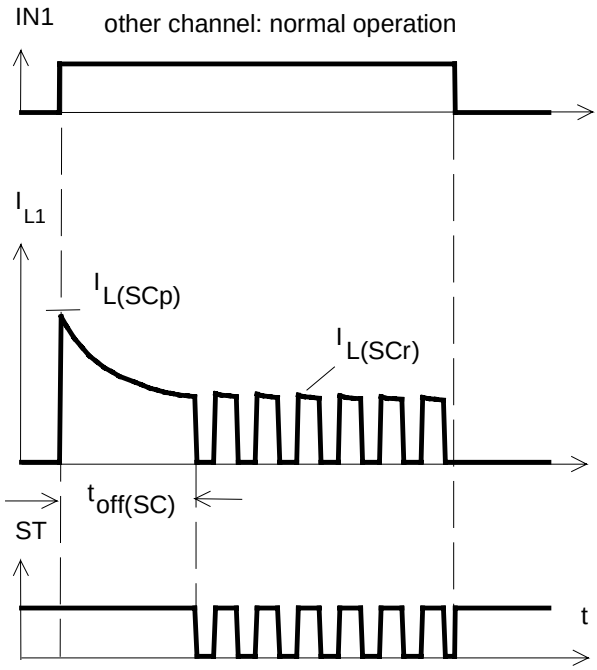


Figure 2a: Switching a lamp:



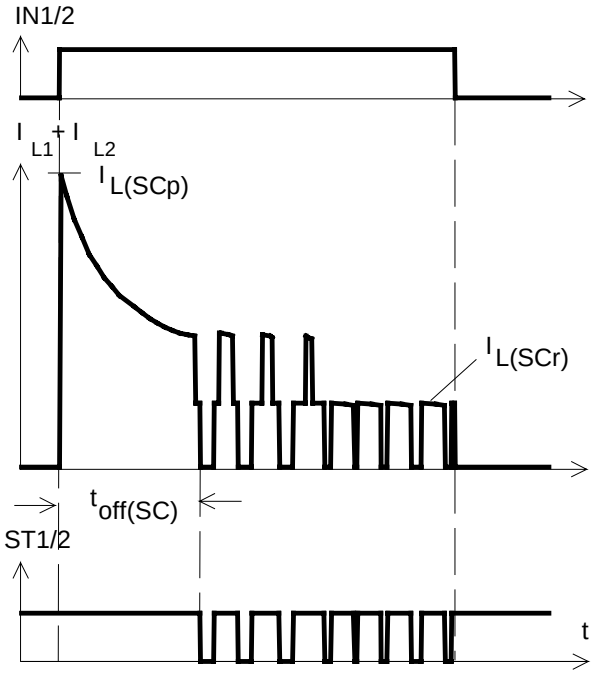
The initial peak current should be limited by the lamp and not by the initial short circuit current $I_{L(SCp)}$ = 28 A typ. of the device.

Figure 3a: Turn on into short circuit:
shut down by overtemperature, restart by cooling



Heating up of the chip may require several milliseconds, depending on external conditions ($t_{off(SC)}$ vs. $T_{j,start}$ see page 10)

Figure 3b: Turn on into short circuit:
shut down by overtemperature, restart by cooling
(two parallel switched channels 1 and 2)



ST1 and ST2 have to be configured as a 'Wired OR' function ST1/2 with a single pull-up resistor.

Figure 4a: Overtemperature:
Reset if $T_j < T_{jt}$

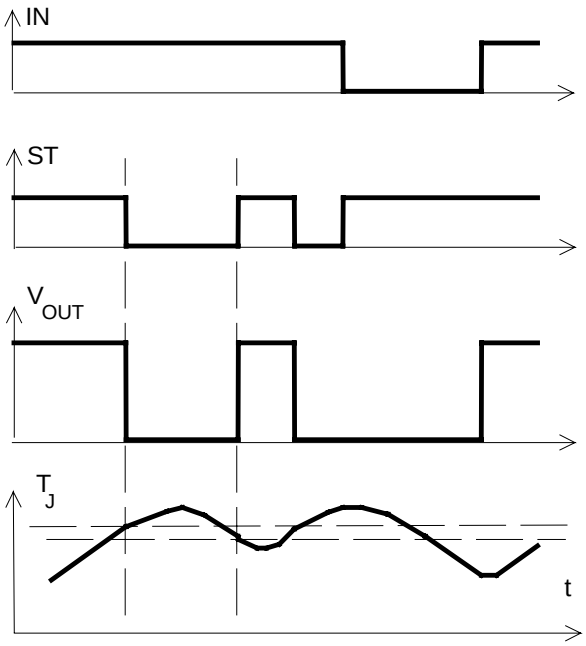


Figure 5a: Open load: detection in ON-state, turn on/off to open load

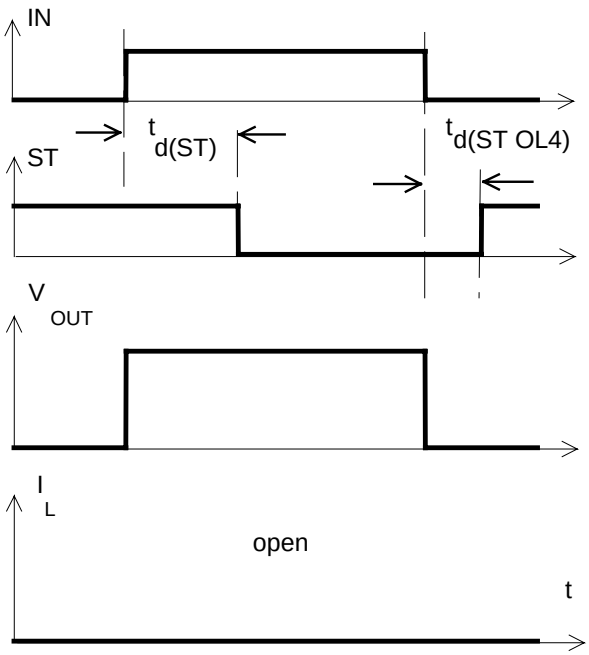
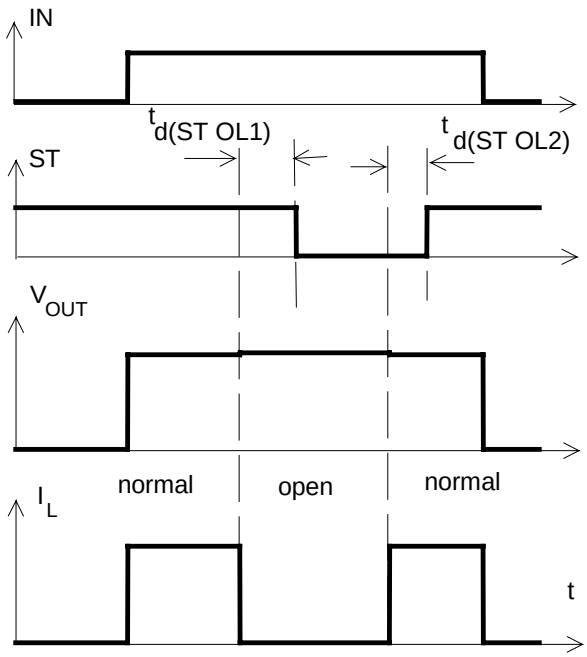


Figure 5b: Open load: detection in ON-state, open load occurs in on-state



$t_{d(ST\ OL1)}$ = 20 µs typ., $t_{d(ST\ OL2)}$ = 10 µs typ

Figure 5c: Open load: detection in ON- and OFF-state (with R_{EXT}), turn on/off to open load

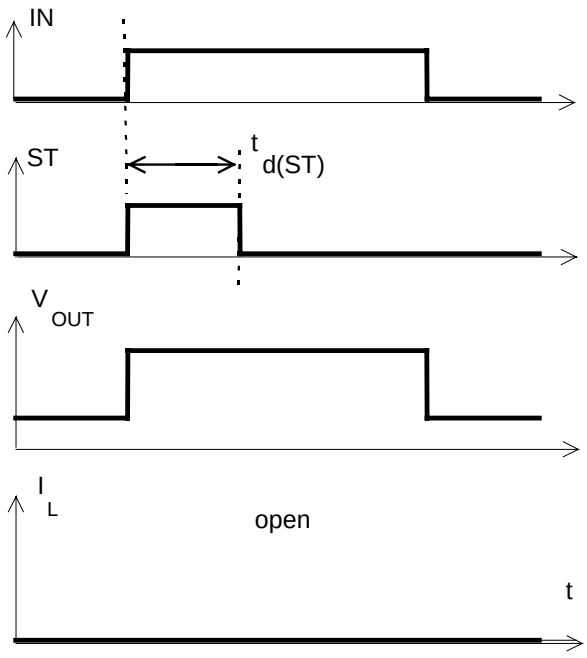


Figure 6a: Undervoltage:

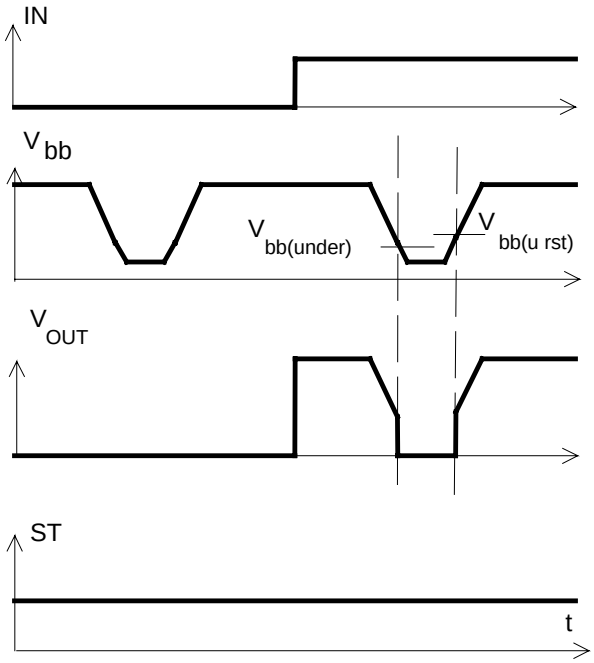
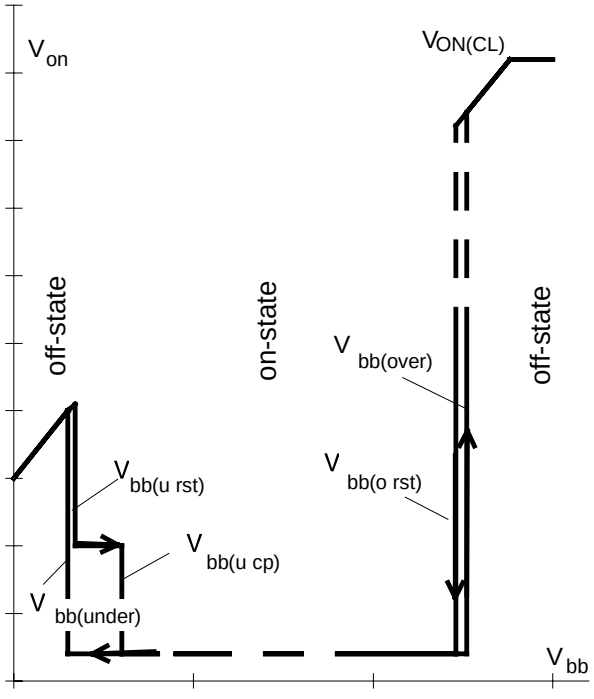
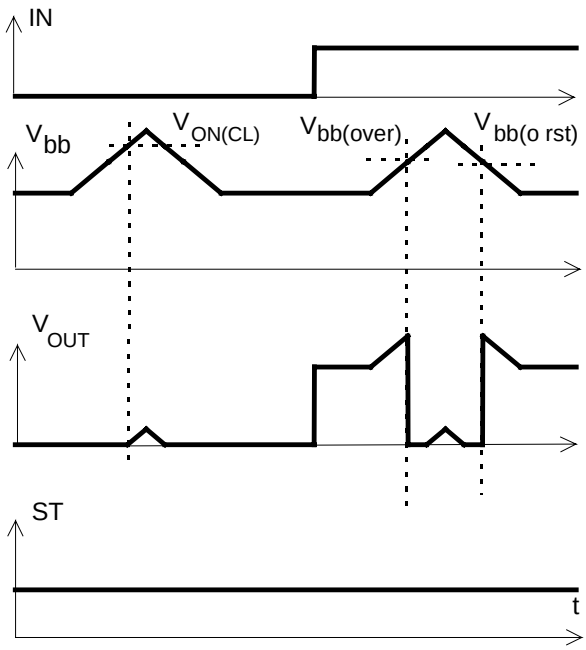


Figure 6b: Undervoltage restart of charge pump



IN = high, normal load conditions.
Charge pump starts at $V_{bb(ucp)}$ = 5.6 V typ.

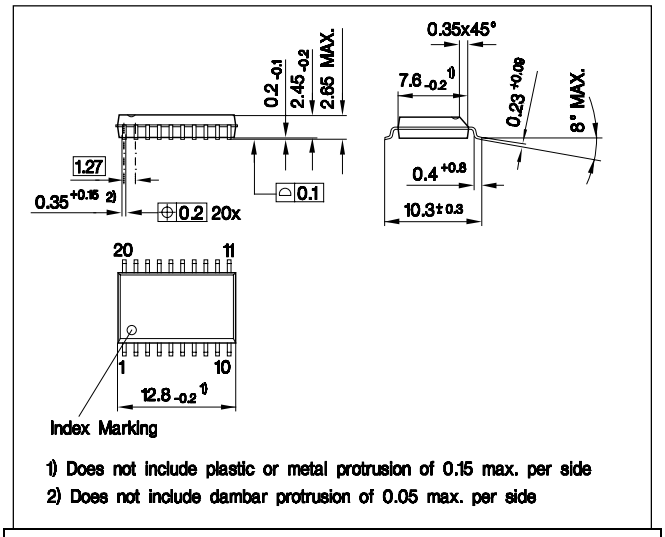
Figure 7a: Overvoltage:



Package and Ordering Code

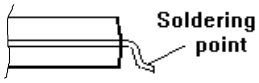
Standard P-DSO-20-9 Ordering Code

BTS725L1	Q67060-S7006-A2



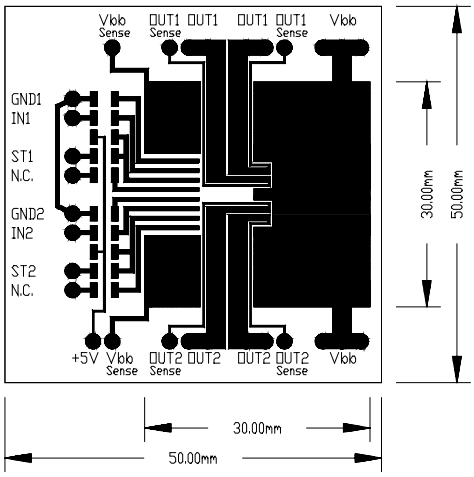
All dimensions in millimetres
1) Does not include plastic or metal protrusions of 0.15 max per side
2) Does not include dambar protrusion of 0.05 max per side

Definition of soldering point with temperature T_S: upper side of solder edge of device pin 15.



Pin 15

Printed circuit board (FR4, 1.5mm thick, one layer 70µm, 6cm² active heatsink area) as a reference for max. power dissipation P_{tot}, nominal load current $I_{L(NOM)}$ and thermal resistance R_{thja}



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